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LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)				APPLICANT Micron Technology, Inc.	
				FILING DATE January 4, 2001	GROUP 2812
U.S. PATENT DOCUMENTS					
*Examiner Initial	Document Number	Date	Name	Class	Subclass
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FOREIGN PATENT DOCUMENTS					
	Document Number	Date	Country	Class	Subclass
	AB				Translation Yes No
OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)					
ER	AC	<p>"Tunneling Leakage Current In Ultrathin (<4nm) Nitride/Oxide Stack Dielectrics"; Ying Shi, Xiewen Wang, and T.P. Ma; pp. 388-390; IEEE Electron Device Letters; Vol. 19, No. 10, October 1998</p>			
ER	AD	<p>"High Quality Ultra-thin (1.5 nm) TiO₂/Si₃N₄ Gate Dielectric for Deep Sub-micron CMOS Technology"; Xin Guo, Xiewen Wang, Zhijong Luo, T.P. Ma, and T. Tamagawa; 1999 IEEE; IEDM; pp. 137-140</p>			
	AE	<p>"High Quality Ta₂O₅ Gate Dielectrics with $T_{ex,eq} < 10\text{ \AA}$"; H.F. Luan, S.J. Lee, C.H. Lee, S.C. Song, Y.I. Mao, T. Senzaki, D. Roberts, and D.L. Kwong; IEDM; pp. 141-144</p>			
ER	AF	<p>"A Novel High K Inter-Poly Dielectric(IPD), Al₂O₃, for Low Voltage/High Speed Flash Memories; Erasing in msccs at 3.3V"; W.H. Lee, J.T. Clemens, R.C. Keller, and L. Manchanda; 1997 Symposium on VLSI Technology Digest of Technical Papers; pp. 117-118</p>			
ER	AG	<p>"Substrate dependence on the optical properties of Al₂O₃ films grown by atomic layer deposition"; Y. Kim, S.M. Lee, C.S. Park, S.I. Lee, and M.Y. Lee; Appl. Phys. Lett. 71 (25) 22 December 1997; pps 3604-3606</p>			
ER	AH	<p>"The effects of oxidation temperature on the capacitance-voltage characteristics of Oxidized AlN films on Si"; J. Kolodzey, E.A. Chowdhury, G. Qui, J. Olowolafe; C.P. Swann; K.M. Unruh; J. Suehle, R.G. Wilson, J.M. Zavada; Appl. Phys. Lett. 71 (26) 29 December 1997; pp. 3802-3804</p>			
ER	AI	<p>"High K Dielectrics for CMOS and Flash"; L. Manchanda; Extended Abstracts of the 1999 International Conference on Solid State Devices and Materials, Tokyo; pp. 150-151</p>			
	AJ	<p>Article: "High-K Dielectrics for Giga-Scale CMOS and Non-Volatile Memory Technology"; L. Manchanda, G. Aters, and J.P. Han</p>			
EXAMINER <i>Eric Kain</i>	DATE CONSIDERED <i>2/20/01</i>				
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OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)								
	AC	Article: "Application of Al ₂ O ₃ Grown by Atomic Layer Deposition to DRAM and FeRAM"; C.T. Kim, C. Lim, K.M. Kim, M.S. Kim, H.K. Jang, Y.S. Yu and J.S. Roh						
<i>ER</i>	AD	"Aluminum oxide films obtained by electron-beam evaporation"; L.V. Veidenbakh and S. N. Gromova; Sov. J. Opt. Technology. 50 (9) Sept. 1983; © 1984 The Optical Society of America; pp. 566-568						
<i>ER</i>	AE	"Investigation of aluminum oxide films by mass-and IR-spectrometric methods"; S.N. Gromova, E.A. Nikolaeva, and E.V. Prokof'ev; Sov. J. Opt. Technol. 56(11), Nov. 1989; © 1990 The Optical Society of America; pp. 667-669						
<i>ER</i>	AF	"Effect of substrate temperature on density of aluminum oxide films" E.B. Brik; Sov. J. Opt. Technol. 57(1), Jan 1990; © 1990 The Optical Society of America; pp. 50-52						
	AG	Article: Beam Solid Interactions: Fundamentals and Applications; Materials Research Society Symposium Proceedings; Volume 279; pp. 825-830						
	AH	"Effect of Plasma Activation on the Phase Transformations of Aluminum Oxide"; O. Zywitzki, G. Hoechzel; Surface & Coatings Technology; pp. 754-762						
	AI	Article: "Tunability of Intrinsic Stress in SiO _x Dielectric Films Formed By Molecular Beam Deposition"; Naresh Chand, R.R. Kola, J.W. Osenbach, and W.T. Tsang"; pp. 195-200						
<i>ER</i>	AJ	"Rapid thermal oxidation of silicon monoxide"; E. Fogarassy, A. Slaoui, C. Fuchs, and J.L. Regolini; Appl. Phys. Lett. 51(5), 3 August 1987; © 1987 American Institute of Physics; pp. 337-339						
EXAMINER <i>Eric Kuhn</i>				DATE CONSIDERED <i>2/20/02</i>				
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EK	AD		"Low Temperature Ion-Assisted Deposition of Thermally Evaporated Silicon Monoxide"; I.C. Stevenson; Society of Vacuum Coaters; 37th Annual Technical Conference Proceedings (1994); pp. 81-84					
	AE		"Optical Thin Films IV: New Developments"; James D. Rancourt; SPIE - The International Society for Optical Engineering; Volume 2262; pp. 14-21					
EK	AF		Article from IBM Website, Intellectual Property Network; US 5923056: "Electronic components with doped metal oxide dielectric materials and a process for making electronic components with doped metal oxide dielectric material"; Lee; Woo-Hyeong and Manchanda; Lalita; issued 7/13/99					
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